

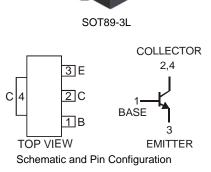


CX56/-16

NPN SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DCX53)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- **Mechanical Data**
- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	Ic	1	A
Peak Pulse Current	I _{CM}	1.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^{\circ}C$	PD	1	W
Operating and Storage Temperature Range	Tj, T _{STG}	-55 to +150	°C
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	R _{0JA}	125	°C/W

Electrical Characteristics @T_A = 25°C unless otherwise specified

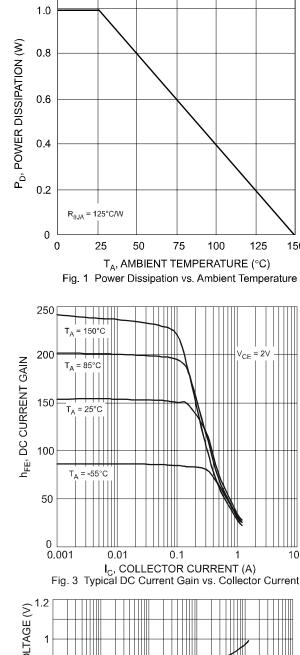
Charao	teristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (N	ote 4)						
Collector-Base Breakdown Vo	ltage	V _{(BR)CBO}	100	_	_	V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown	Voltage	V _{(BR)CEO}	80	_		V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Volt	age	V _{(BR)EBO}	5.0	—		V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector-Base Cutoff Current		I _{CBO}	_	_	0.1 20	μA	V _{CB} = 30V, I _E = 0 V _{CB} = 30V, I _E = 0, T _A = 150°C
Emitter-Base Cutoff Current		I _{EBO}		_	100	nA	$V_{EB} = 5.0V, I_{C} = 0$
ON CHARACTERISTICS (No	te 4)					_	
DC Current Gain	DCX56, DCX56-16	h _{FE}	63 40	_		—	$I_{C} = 5.0 \text{mA}, V_{CE} = 2.0 \text{V}$ $I_{C} = 500 \text{mA}, V_{CE} = 2.0 \text{V}$
	DCX56		63		250		I _C = 150mA, V _{CE} = 2.0V
	DCX56-16		100		250	_	I _C = 150mA, V _{CE} = 2.0V
Collector-Emitter Saturation V	oltage	V _{CE(SAT)}		_	0.5	V	$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}$
Base-Emitter Turn-On Voltage	9	V _{BE(ON)}		_	1.0	V	I _C = 500mA, V _{CE} = 2.0V
SMALL SIGNAL CHARACTE	RISTICS						
Current Gain-Bandwidth Prod	uct	f _T	_	200	_	MHz	I _C = 50mA, V _{CE} = 5V, f = 100MHz
Output Capacitance		Cobo		_	15	pF	$V_{CB} = 10V, I_E = 0, f = 1MHz$

2.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. 3.

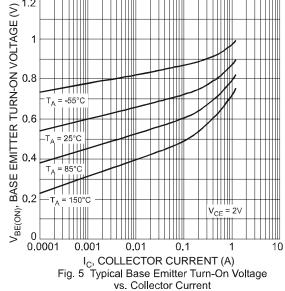
Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$. 4.

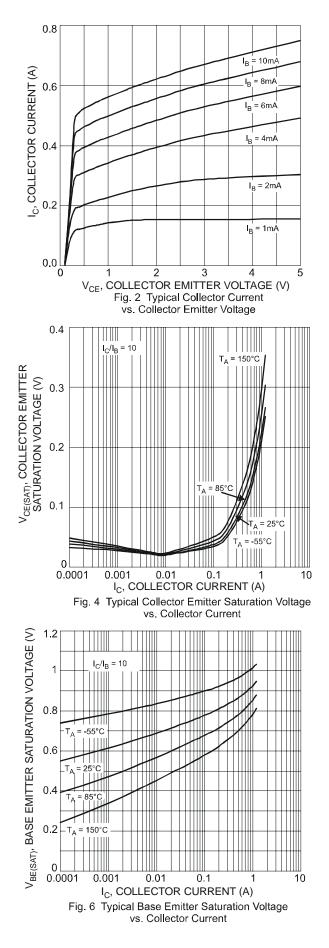




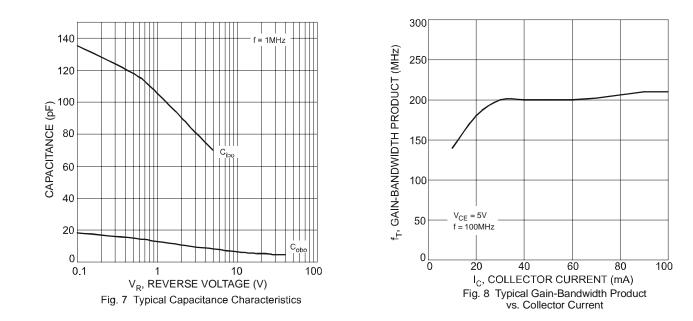
150

10







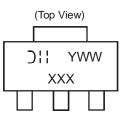


Ordering Information (Note 5)

Device	Packaging	Shipping
DCX56-13	SOT89-3L	2500/Tape & Reel
DCX56-16-13	SOT89-3L	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information

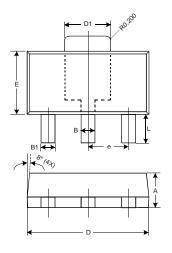


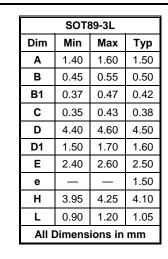
XXX = Product Type Marking Code ex. N18 = DCX56

N18-16 = DCX56-16

D'II = Manufacturer's code marking
YWW = Date Code Marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

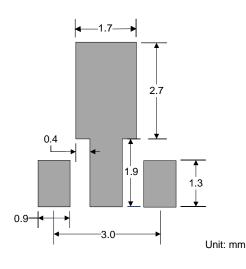
Package Outline Dimensions







Suggested Pad Layout



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RN1607(TE85L,F) DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TETL DTC115TKAT146 DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G NSBA114TDP6T5G NSBA143ZF3T5G NSBC114YF3T5G NSBC123TF3T5G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G NSBC114TF3T5G NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVDTC143ZM3T5G SMUN5216DW1T1G NSVMUN5312DW1T2G NSVMUN5215DW1T1G